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The 17th International Conference on Molecular Beam Epitaxy

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Contents

The 17th International Conference on Molecular Beam Epitaxy

Conference Information	1
Preface	3
MBE fundamentals	
Size-dependent contact angle of Ga droplets on GaAs M. Jo, T. Mano, Y. Sakuma and K. Sakoda	5
Correlation between adatom dynamics and electron accumulation at the epitaxial InAs(111)A surface K. Kanisawa	8
<i>Ab initio</i> -based approach to novel behavior of InAs wetting layer surface grown on GaAs(001) T. Ito, K. Hirai, T. Akiyama and K. Nakamura	13
Plasma-assisted molecular beam epitaxy process combined with a liquid phase electroepitaxy, a novel method for the growth of GaN layers S.V. Novikov, R.E.L. Powell, A.J. Kent and C.T. Foxon	17
<i>Ab initio</i> -based approach to initial incorporation of Bi on GaAs(001)-c(4×4) _α surface I. Murase, T. Akiyama, K. Nakamura and T. Ito	21
Quantitative study of microtwins in GaP/Si thin film and GaAsPN quantum wells grown on silicon substrates T. Nguyen Thanh, C. Robert, E. Giudicelli, A. Létoublon, C. Cornet, A. Ponchet, T. Rohel, A. Balocchi, J.S. Micha, M. Perrin, S. Loualiche, X. Marie, N. Bertru, O. Durand and A. Le Corre	25
<i>Ab initio</i> -based approach to incorporation of N atoms on GaAs(001) surfaces T. Sugitani, T. Akiyama, K. Nakamura and T. Ito	29
In situ three-dimensional X-ray reciprocal-space mapping of GaAs epitaxial films on Si(001) M. Takahashi, Y. Nakata, H. Suzuki, K. Ikeda, M. Kozu, W. Hu and Y. Ohshita	34
Direct stress measurement of Si(111) 7×7 reconstruction H. Asaoka, T. Yamazaki, Y. Yokoyama and K. Yamaguchi	37
As flux dependence on RHEED transients during InAs quantum dot growth K. Shimomura, T. Shirasaka, D.M. Tex and I. Kamiya	41
<i>In situ</i> STM observations of step structures in a trench around an InAs QD at 300°C T. Toujyou, T. Otsu, D. Wakamatsu, M. Kurisaka, T. Konishi and S. Tsukamoto	44
Mechanism of selective area growth of InP on Si(001) substrates using SiO ₂ mask by gas-source molecular beam epitaxy S. Hasegawa, T. Shimoi and H. Asahi	47
Incorporation of Mn atoms into the GaAs(110) surface M. Hirayama and S. Tsukamoto	50
Self-assembly of Ga droplets attached to GaAs quantum dots M. Elborg, T. Noda, T. Mano, M. Jo, Y. Sakuma and K. Sakoda	53
III-V and dilute Nitrides	
Photocapacitance study of MBE grown GaInNAsSb thin film solar cells M.M. Islam, N. Miyashita, N. Ahsan, T. Sakurai, K. Akimoto and Y. Okada	57

Photoluminescence dynamics of excitons at the mini-Brillouin-zone edge in a GaAs/AlAs superlattice M. Nakayama, T. Yamashita and T. Hasegawa	61
Effects of growth temperature and buffer scheme on characteristics of InP-based metamorphic InGaAs photodetectors Y. Gu, Y.G. Zhang, K. Wang, X. Fang, C. Li, L. Zhou, A.Z. Li and Hsby. Li	65
Optical properties of InAsSbN single quantum wells grown on InP substrates for 2- μ m-wavelength region T. Shono, S. Mizuta and Y. Kawamura	69
Quantitative estimation of density of Bi-induced localized states in GaAs _{1-x} Bi _x grown by molecular beam epitaxy M. Yoshimoto, M. Itoh, Y. Tominaga and K. Oe	73
Problems in low-temperature grown polycrystalline InAs layers on glass and their relief by inserting GaSbAs buffer layers Y. Kajikawa, T. Okuzako and Y. Matsui	77
Crystalline and electrical characteristics of C ₆₀ uniformly doped GaAs layers J. Nishinaga and Y. Horikoshi	81
Molecular beam epitaxy of ErGaAs alloys on GaAs (001) substrates R.G. Jin, S. Yagi, Y. Hijikata, S. Kuboya, K. Onabe, R. Katayama and H. Yaguchi	85
MBE growth and characterization of (100) and (631)-oriented modulation doped AlGaAs/GaAs heterostructures V.H. Mendez-Garcia, J.V. González-Fernández, L.I. Espinosa-Vega, T. Díaz, R. Romano, E. Rosendo, S. Gallardo, D. Vázquez-Cortes and S. Shimomura	88
Co-doping of In _x Ga _{1-x} As with silicon and tellurium for improved ultra-low contact resistance J.J.M. Law, A.D. Carter, S. Lee, C.-Y. Huang, H. Lu, M.J.W. Rodwell and A.C. Gossard	92
Growth of dilute BGaP alloys by molecular beam epitaxy N. Urakami, F. Fukami, H. Sekiguchi, H. Okada and A. Wakahara	96
Determination of surface electric potential by photoreflectance spectroscopy of HEMT heterostructures L. Zamora-Peredo, I.E. Cortes-Mestizo, L. García-González, J. Hernández-Torres, D. Vázquez-Cortes, S. Shimomura, A.C.-d.l. Rosa and V.H. Méndez-García	100
Polarized Raman spectroscopy of corrugated MBE grown GaAs ($\bar{6}\bar{3}\bar{1}$) homoepitaxial films L.I. Espinosa-Vega, A.G. Rodriguez, E. Cruz-Hernandez, I. Martinez-Veliz, J. Rojas-Ramirez, M. Ramirez-Lopez, J. Nieto-Navarro, M. Lopez-Lopez and V.H. Mendez-Garcia	105
Heterointegration by molecular beam epitaxy: (In,Ga)As/GaAs quantum wells on GaAs, Ge, Ge/Si and Ge/Si pillars M. Richter, E. Uccelli, A.G. Taboada, D. Caimi, N. Daix, M. Sousa, C. Marchiori, H. Siegart, C.V. Falub, H. von Känel, F. Isa, G. Isella, A. Pezous, A. Dommann, P. Niedermann and J. Fompeyrine	109
Sb irradiation effect on growth of GaAs thin film on Si (111) substrate O. Morohara, H. Geka, Y. Moriyasu and N. Kuze	113
Growth of heterostructures on InAs for high mobility device applications R. Contreras-Guerrero, S. Wang, M. Edirisooriya, W. Priyantha, J.S. Rojas-Ramirez, K. Bhuwalka, G. Doornbos, M. Holland, R. Oxland, G. Vellianitis, M. Van Dal, B. Duriez, M. Passlack, C.H. Diaz and R. Droopad	117
Type-II InAs/GaSb superlattice grown on InP substrate K. Miura, Y. Iguchi and Y. Kawamura	121
Semi-insulating InP:Fe for buried-heterostructure strain-compensated quantum-cascade lasers grown by gas-source molecular-beam epitaxy M.P. Semtsiv, A. Aleksandrova, M. Elagin, G. Monastyrskiy, J.-F. Kischkat, Y.V. Flores and W.T. Masselink	125

Study of Sb template for heteroepitaxial growth of GaSb thin film on Si(111) substrate H. Toyota, A. Okabe, T. Endoh, Y. Jinbo and N. Uchitomi	129
InGaAs/AlAs/InAlAs coupled double quantum wells for intersubband transition devices operating at 1550 nm S.-i. Gozu, T. Mozume, H. Kuwatsuka and H. Ishikawa	134
Growth and characterization of GaDyN/GaN double barrier structures M. Sano, Y.K. Zhou, S. Emura, S. Hasegawa and H. Asahi	137
Growth of metamorphic InGaP layers on GaAs substrates J.Y. Yan, Q. Gong, L. Yue, Q.B. Liu, R.H. Cheng, C.F. Cao, Y. Wang and S.M. Wang	141
A calibration method for group V fluxes and impact of V/III flux ratio on the growth of InAs/InAsSb type-II superlattices by molecular beam epitaxy H. Li, S. Liu, O.O. Cellek, D. Ding, X.-M. Shen, E.H. Steenbergen, J. Fan, Z. Lin, Z.-Y. He, Q. Zhang, P.T. Webster, S.R. Johnson, L. Ouyang, D.J. Smith and Y.-H. Zhang	145
Electroluminescence of GaNAs/GaAs MQWs p-i-n junctions grown by RF-MBE using modulated nitrogen radical beam source N. Ohta, K. Arimoto, M. Shiraga, K. Ishii, M. Inada, S. Yanai, Y. Nakai, H. Akiyama, T. Mochizuki, T. Takahashi, N. Takahashi, H. Miyagawa, N. Tsurumachi, S. Nakanishi and S. Koshiba	150
IV, II-VI, and Oxides	
Characteristics of CuGaSe ₂ layers grown on GaAs substrates M. Fujita, A. Kawaharazuka and Y. Horikoshi	154
Growth mechanism of CuZnInSe ₂ thin films grown by molecular beam epitaxy Y.H. Tseng, C.S. Yang, C.H. Wu, J.W. Chiu, M.D. Yang and C.-H. Wu	158
Characterization of Cu(In,Ga)Se ₂ grown by MBE by two-wavelength excited photoluminescence spectroscopy A. Gupta, N. Hiraoka, T. Sakurai, A. Yamada, S. Ishizuka, S. Niki and K. Akimoto	162
Electronic and transport properties of Eu-substituted infinite-layer strontium ferrite thin films A. Chikamatsu, T. Matsuyama, T. Katayama, Y. Hirose, H. Kumigashira, M. Oshima, T. Fukumura and T. Hasegawa	165
Rock-salt Zn _{1-x} Mg _x O epilayer having high Zn content grown on MgO (100) substrate by plasma-assisted molecular beam epitaxy C.-Y. Lu, T. Yan, L. Chang, K.H. Ploog, M.M.C. Chou and C.-M. Chiang	168
Epitaxial growth of nonpolar ZnO on MgO (1 0 0) substrate by molecular beam epitaxy C.-Y. Lu, L. Chang, K.H. Ploog and M.M.C. Chou	172
Growth and application of epitaxial heterostructures with polymorphous rare-earth oxides R. Dargis, A. Clark, E. Arkun, R. Roucka, R. Smith, A.A. Demkov and M. Lebby	177
Optical and electrical properties of ZnSeO alloys grown by plasma-assisted molecular beam epitaxy C.-Y. Chen, C.-Y. Yang, J.-I. Chyi and C.-H. Wu	180
Multi-source MBE with high-precision rate control system as a synthesis method <i>sui generis</i> for multi-cation metal oxides H. Yamamoto, Y. Krockenberger and M. Naito	184
Lattice and grain-boundary diffusions of impurity atoms in BaSi ₂ epitaxial layers grown by molecular beam epitaxy K. Nakamura, K. Toh, M. Baba, M. Ajmal Khan, W. Du, K. Toko and T. Suemasu	189
Formation of large-grain-sized BaSi ₂ epitaxial layers grown on Si(111) by molecular beam epitaxy M. Baba, K. Toh, K. Toko, K.O. Hara, N. Usami, N. Saito, N. Yoshizawa and T. Suemasu	193

Large photoresponsivity in semiconducting BaSi_2 epitaxial films grown on Si(001) substrates by molecular beam epitaxy S. Koike, K. Toh, M. Baba, K. Toko, K.O. Hara, N. Usami, N. Saito, N. Yoshizawa and T. Suemasu	198
Molecular beam epitaxy of boron doped p -type BaSi_2 epitaxial films on Si(111) substrates for thin-film solar cells M. Ajmal Khan, K.O. Hara, K. Nakamura, W. Du, M. Baba, K. Toh, M. Suzuno, K. Toko, N. Usami and T. Suemasu	201
Rutherford backscattering studies of strain-relaxed SiGe films grown on Si substrate with compositionally graded buffer layers Y. Watanabe, R. Oshima, I. Sakata, K. Matsubara and I. Sakamoto	205
Thermal-activated carrier transfer in ZnCdO thin film grown by plasma-assisted molecular beam epitaxy K.F. Chien, W.L. Hsu, A.J. Tzou, Y.C. Lin, W.C. Chou, L. Lee, C.H. Chia and C.S. Yang	208
Gas-source MBE growth of strain-relaxed $\text{Si}_{1-x}\text{C}_x$ on Si(100) substrates K. Arimoto, S. Sakai, H. Furukawa, J. Yamanaka, K. Nakagawa, N. Usami, Y. Hoshi, K. Sawano and Y. Shiraki	212
Optical properties of $\text{Zn}_{1-x}\text{Mn}_x\text{O}$ thin films grown by molecular beam epitaxy K.F. Chien, Y.L. Yang, A.J. Tzou and W.C. Chou	218
Growth evolution and magneto-optical characteristics of self-assembled ZnTe/ZnMnSe quantum dots L. Lee, W.-C. Fan, K.-F. Chien, A.-J. Tzou and W.-C. Chou	222
High-quality SiGe films grown with compositionally graded buffer layers for solar cell applications R. Oshima, Y. Watanabe, M. Yamanaka, H. Kawanami, I. Sakamoto, K. Matsubara and I. Sakata	226
Change of Si(110) reconstructed structure by Ge nanocluster formation Y. Yokoyama, T. Yamazaki and H. Asaoka	230
Growth of II–VI ZnSe/CdSe nanowires for quantum dot luminescence E. Bellet-Amalric, M. Elouneq-Jamroz, P. Rueda-Fonseca, S. Bounouar, M.D. Hertog, C. Bougerol, R. André, Y. Genuist, J.P. Poizat, K. Kheng, J. Cibert and S. Tatarenko	233
Interface properties of MBE grown epitaxial oxides on GaAs R. Contreras-Guerrero, M. Edirisooriya, O.C. Noriega and R. Droopad	238
Solid phase epitaxy of EuTiO_3 thin films on SrTiO_3 (100) substrates with different oxygen contents K. Shimamoto, Y. Hirose, S. Nakao, T. Fukumura and T. Hasegawa	243
Effects of different substrate surface modifications on the epitaxial ZnO/Si P. Wang, C. Jin, H. Zhan, X. Chen, F. Xu, Y. Zhou, H. Wang and J. Kang	246
On the origin of the uniaxial strain induced in Si/Ge heterostructures with selective ion implantation technique K. Sawano, Y. Hoshi, S. Nagakura, K. Arimoto, K. Nakagawa, N. Usami and Y. Shiraki	251
Strain relaxation of thin Ge films on Si(001) grown by carbon-mediated epitaxy D. Tetzlaff, T.F. Wietler, E. Bugiel and H.J. Osten	254
Molecular beam epitaxial growth of ZnCdTeO epilayers for intermediate band solar cells T. Tanaka, Y. Nagao, T. Mochinaga, K. Saito, Q. Guo, M. Nishio, K.M. Yu and W. Walukiewicz	259
Proposal of BeZnTe/ZnSeTe superlattice quasi-quatennaries on InP substrates for yellow/green light emitting devices T. Kobayashi, I. Nomura, K. Murakami and K. Kishino	263
MBE growth and characterization of a II–VI distributed Bragg reflector and microcavity lattice-matched to MgTe J.-G. Rousset, J. Kobak, T. Slupinski, T. Jakubczyk, P. Stawicki, E. Janik, M. Tokarczyk, G. Kowalski, M. Nawrocki and W. Pacuski	266

On the structural properties of MgS-rich II–VI-based microcavities S. Klembt, K. Frank, G. Qian, T. Klein, A. Rosenauer, D. Hommel and C. Kruse	270
Ultra low density of CdTe quantum dots grown by MBE J. Kobak, J.-G. Rousset, R. Rudniewski, E. Janik, T. Slupinski, P. Kossacki, A. Golnik and W. Pacuski	274
Nitrides	
MBE fabrication of III-N-based laser diodes and its development to industrial system C. Skierbiszewski, M. Siekacz, H. Turski, G. Muziol, M. Sawicka, P. Perlin, Z.R. Wasilewski and S. Porowski	278
Origin of tensile strain in GaN grown on AlGa _N /AlN stress mitigating layers on 100-mm Si (1 1 1) by ammonia molecular beam epitaxy M. Agrawal, N. Dharmarasu, K. Radhakrishnan and L. Ravikiran	283
Cubic GaN quantum dots embedded in zinc-blende AlN microdisks M. Bürger, R.M. Kemper, C.A. Bader, M. Ruth, S. Declair, C. Meier, J. Förstner and D.J. As	287
Growth of cubic GaN on 3C–SiC/Si (001) nanostructures R.M. Kemper, L. Hiller, T. Stauden, J. Pezoldt, K. Duschik, T. Niendorf, H.J. Maier, D. Meertens, K. Tillmann, D.J. As and J.K.N. Lindner	291
Study of the pseudo-(1×1) surface by RHEED and XPS for InGa _N /Ga _N (0001)/Al ₂ O ₃ heterostructures grown by PA-MBE E. Cruz-Hernández, M. Ramirez-Lopez, M. Pérez-Caro, P.G. Mani-Gonzalez, A. Herrera-Gómez, A.Y. Gorbachev, M. López-López and V.H. Méndez-García	295
Deep level defects in Ga- and N-polarity GaN grown by molecular beam epitaxy on si(111) K.R. Peta, S.-T. Lee, K. Moon-Deock, J.-E. Oh, S.-G. Kim and T.-G. Kim	299
Coalescence of <i>a</i> -plane GaN stripes in low angle incidence microchannel epitaxy by ammonia-based metal-organic molecular beam epitaxy S. Naritsuka, C.H. Lin, S. Uchiyama and T. Maruyama	303
RF-MBE growth of cubic AlN on MgO (001) substrates via 2-step c-GaN buffer layer M. Kakuda, S. Morikawa, S. Kuboya, R. Katayama, H. Yaguchi and K. Onabe	307
Photoluminescence properties in GaGdN grown on GaN(0001) by PA-MBE K. Higashi, S. Hasegawa, S. Sano, Y.K. Zhou and H. Asahi	310
Growth parameter dependence of structural, electrical and magnetic properties in GaGdN layers grown on GaN(0001) S. Sano, S. Hasegawa, Y. Mitsuno, K. Higashi, M. Ishimaru, T. Sakurai, H. Ohta and H. Asahi	314
Control of threading dislocation density at the initial growth stage of AlN on c-sapphire in plasma-assisted MBE D.V. Nechaev, P.A. Aseev, V.N. Jmerik, P.N. Brunkov, Y.V. Kuznetsova, A.A. Sitnikova, V.V. Ratnikov and S.V. Ivanov	319
Spintronics and Novel Materials	
Molecular beam epitaxy growth of InSb _{1-x} Bi _x thin films Y. Song, S. Wang, I. Saha Roy, P. Shi, A. Hallen and Z. Lai	323
Origin of cooperative transition of antisite-Arsenic defects in Be-doped low-temperature-grown GaAs layers M.A. Mohamed, P.T. Lam and N. Otsuka	329
Graphene films grown at low substrate temperature and the growth model by using MBE technique M.-Y. Lin, W.-C. Guo, M.-H. Wu, P.-Y. Wang, S.-C. Lee and S.-Y. Lin	333
Coexistence of magnetic domains with in-plane and out-of-plane anisotropy in a single GaMnAs film S. Lee, H. Lee, T. Yoo, S. Lee, X. Liu and J.K. Furdyna	337

Epitaxial growth of ferromagnetic $\text{Co}_x\text{Fe}_{4-x}\text{N}$ thin films on SrTiO_3 (001) and magnetic properties T. Sanai, K. Ito, K. Toko and T. Suemasu	342
Growth of pentacene crystallinity control layers for high mobility organic field-effect transistors based on benzodithiophene-dimer films T. Sakai, Y. Matsumoto, K. Shibamoto, H. Osuga, K. Uno and I. Tanaka	347
Crystal growth of magnetic dihydride $\text{Gd}_x\text{Y}_{1-x}\text{H}_2$ for generation of spin current T. Sakuraba, H. Hirama, M. Sakai, Z. Honda, M. Hayakawa, T. Okoshi, A. Kitajima, A. Oshima, K. Higuchi and S. Hasegawa	351
Enhancement of hydrogen uptake for Y and Gd films by thin Ni surface overlayers H. Hirama, M. Hayakawa, T. Okoshi, M. Sakai, K. Higuchi, A. Kitajima, A. Oshima and S. Hasegawa	356
Planar Hall effect in a single GaMnAs film grown on Si substrate J. Won, J. Shin, S. Lee, H. Lee, T. Yoo, S. Lee, X. Liu and J.K. Furdyna	361
Effect of atomic-hydrogen irradiation on reduction of residual carrier concentration in $\beta\text{-FeSi}_2$ films grown on Si substrates by atomic-hydrogen-assisted molecular beam epitaxy Y. Funase, M. Suzuno, K. Toko and T. Suemasu	365
Fabrication and characterization of DH- α 6T monolayer film on silicon dioxide R. Ye, Y. Fujinaka, K. Ohata and M. Baba	368
Growth of high-quality CuCl thin films by a technique involving electron-beam irradiation M. Ichimiya, P. Le Quang, M. Ashida and T. Itoh	372
Growth condition dependence of Ge-doped $\beta\text{-FeSi}_2$ epitaxial film by molecular beam epitaxy K. Noda, Y. Terai and Y. Fujiwara	376
Control of magnetic anisotropy in (Ga,Mn)As with etching depth of specimen boundaries Y. Hashimoto, Y. Iye and S. Katsumoto	381
Spin-injection into epitaxial graphene on silicon carbide K. Konishi, Z. Cui, T. Hiraki and K. Yoh	385
Influence of hydrogen incorporation on texture and grain size in YH_2 films T. Okoshi, M. Hayakawa, H. Hirama, M. Sakai, K. Higuchi, A. Kitajima, A. Oshima and S. Hasegawa	388
Dynamics of electron-spin injection in a heterovalent GaAs/AlGaAs/ZnMnSe structure with a coupled double quantum well of GaAs/AlGaAs Y. Kuno, T. Sasaki, T. Kiba, V.Kh. Kaibyshev, F. Liaci, A.A. Toropov, S.V. Ivanov and A. Murayama	393
STM observation of MnAs initial growth surface on GaAs(001)- $c(4\times 4)\alpha$ and 6×6 reconstructions M. Hiraoka, S. Kaku and J. Yoshino	397
Suppression of Andreev current due to transverse current flow in an InAs two-dimensional electrons Y. Takahashi, Y. Hashimoto, Y. Iye and S. Katsumoto	400
Molecular beam epitaxial growth of graphene using cracked ethylene F. Maeda and H. Hibino	404
Studies of zinc-blende type MnAs thin films grown on InP(001) substrates by XRD H. Oomae, S. Irizawa, Y. Jinbo, H. Toyota, T. Kambayashi and N. Uchitomi	410
Effect of Ag-doped bathocuproine on the recombination properties of exciton in fullerene S. Wang, T. Sakurai, K. Komatsu and K. Akimoto	415
Thickness dependence of magnetic anisotropy in MnSb epitaxial layers N. Nishizawa and H. Munekata	418

Nano-structures

Wideband luminescence of high-density InAs quantum dots on GaAsSb/GaAs layers Y. Osaka, H. Tanabe, K. Yamada and K. Yamaguchi	422
Temperature-dependent photoluminescence and carrier dynamics of standard and coupled type-II GaSb/GaAs quantum rings W.-H. Lin, K.-W. Wang, S.-Y. Lin and M.-C. Wu	426
In(Ga)As quantum dots on InGaP layers grown by solid-source molecular beam epitaxy T. Sugaya, R. Oshima, K. Matsubara and S. Niki	430
InGaAs quantum-dot-in-ring structure by droplet epitaxy P. Boonpeng, S. Kiravittaya, S. Thainoi, S. Panyakeow and S. Ratanathammaphan	435
Optical and structural studies of highly uniform Ge quantum dots on Si (001) substrate grown by solid-source molecular beam epitaxy K. Gotoh, R. Oshima, T. Sugaya, I. Sakata, K. Matsubara and M. Kondo	439
Structural properties of ultra-low density nanoholes for the generation of well-separated GaAs quantum dots D. Sonnenberg, A. Graf, V. Paulava, W. Hansen and Ch. Heyn	442
GaAs nanopillars by self-assembled droplet etching Ch. Heyn, D. Sonnenberg, Th. Bartsch, A. Wetzel, J. Kerbst and W. Hansen	446
Fabrication of low-density self-assembled InAs quantum dots on InP(311)B substrate by molecular beam epitaxy K. Akahane and N. Yamamoto	450
RF-MBE growth of cubic InN nano-scale dots on cubic GaN J. Suzuki, M. Orihara, S. Yagi, Y. Hijikata and H. Yaguchi	454
Molecular beam epitaxial growths of high-optical-gain InAs quantum dots on GaAs for long-wavelength emission K. Nishi, T. Kageyama, M. Yamaguchi, Y. Maeda, K. Takemasa, T. Yamamoto, M. Sugawara and Y. Arakawa	459
Observation of optical anisotropy of highly uniform InAs quantum dots M. Uemura, J. Ohta, R. Yamaguchi, K. Yamaguchi and A. Tackeuchi	463
The study of self-assembled ZnO nanorods grown on Si(111) by plasma-assisted molecular beam epitaxy A.J. Tzou, K.F. Chien, H.Y. Lai, J.T. Ku, L. Lee, W.C. Fan and W.C. Chou	466
Temperature dependence of photoluminescence for site-controlled InAs/GaAs quantum dot chains T.V. Hakkarainen, A. Schramm, E. Luna, J. Tommila and M. Guina	470
Growth of GaSb quantum dots on GaAs (311)A T. Kawazu, T. Noda, T. Mano, Y. Sakuma and H. Sakaki	475
Selective area growth of InAs nanostructures on faceted GaAs microstructures by migration enhanced epitaxy M. Zander, J. Nishinaga and Y. Horikoshi	480
Ultrafast photocarrier relaxation processes in Er-doped InAs quantum dots embedded in strain-relaxed InGaAs barriers T. Kitada, H. Ueyama, K. Morita and T. Isu	485
Self-organization and photoluminescence properties of $Pb_{0.7}Sn_{0.3}Te$ quantum dots embedded in a CdTe matrix K. Koike, A. Iwamoto and M. Yano	489
Surface/interface-related optical properties in Si nanodisks fabricated by neutral-beam etching using bio-templates T. Kiba, K. Suzaki, H. Li, M. Igarashi, S. Samukawa and A. Murayama	493

Effects of As pressure on the quality of GaAs/AlGaAs quantum dots grown on silicon by droplet epitaxy S. Bietti, L. Cavigli, S. Minari, S. Adorno, G. Isella, A. Vinattieri, M. Gurioli and S. Sanguinetti	497
Growth of InAs/GaAs quantum dots with central emission wavelength of 1.05 μm using In-flush technique for broadband near-infrared light source Y. Hino, N. Ozaki, S. Ohkouchi, N. Ikeda and Y. Sugimoto	501
Controlled wurtzite inclusions in self-catalyzed zinc blende III–V semiconductor nanowires T. Rieger, M.I. Lepsa, T. Schäpers and D. Grützmacher	506
Fabrication and characterization of a δ -dope InAs/InP core shell nanowire transistor Z. Cui, T. Ishikura, F. Jabeen, J.-C. Harmand and K. Yoh	511
Annealing induced anisotropy in GaAs/AlGaAs quantum dots grown by droplet epitaxy S. Adorno, S. Bietti and S. Sanguinetti	515
InP _{1-x} As _x quantum dots in InP nanowires: A route for single photon emitters J.-C. Harmand, F. Jabeen, L. Liu, G. Patriarche, K. Gauthron, P. Senellart, D. Elvira and A. Beveratos	519
Polarization anisotropy of stacked InAs quantum dots on InGaAs/GaAs cross-hatch patterns T. Chokamnuai, P. Rattanadon, S. Thainoi, S. Panyakeow and S. Kanjanachuchai	524
Fabrication of InAs nanoscale rings by droplet epitaxy T. Noda, M. Jo, T. Mano, T. Kawazu and H. Sakaki	529
Comparison of Be-doped GaAs nanowires grown by Au- and Ga-assisted molecular beam epitaxy D.L. Dheeraj, A.M. Munshi, O.M. Christoffersen, D.C. Kim, G. Signorello, H. Riel, A.T.J. van Helvoort, H. Weman and B.O. Fimland	532
Infrared emitting property and spherical symmetry of colloidal PbS quantum dots S. Nakashima, K. Kikushima and K. Mukai	537
Thiol-stabilized PbS quantum dots with stable luminescence in the infrared spectral range S. Nakashima, A. Hoshino, J. Cai and K. Mukai	542
Phase coherent transport in GaAs/AlGaAs core-shell nanowires D. Lucot, F. Jabeen, M.R. Ramdani, G. Patriarche, G. Faini, D. Maily and J.-C. Harmand	546
Shape evolution of low density InAs quantum dots in the partial capping process by using As ₂ source S. Ohkouchi, N. Kumagai, K. Watanabe, S. Iwamoto and Y. Arakawa	549
Extending emission wavelength of InAs/GaAs quantum dots beyond 1.3 μm by using quantum dot bi-layer for broadband light source N. Ozaki, Y. Nakatani, S. Ohkouchi, N. Ikeda, Y. Sugimoto, K. Asakawa, E. Clarke and R.A. Hogg	553
Rim formation on non-elongated InAs quantum dots grown by partial cap and annealing process at low temperature N. Kumagai, S. Ohkouchi, K. Watanabe, S. Iwamoto and Y. Arakawa	558
Non-VLS growth of GaAs nanowires on silicon by a gallium pre-deposition technique J. Kwoen, K. Watanabe, S. Iwamoto and Y. Arakawa	562
Devices	
InGaN/GaN self-organized quantum dot lasers grown by molecular beam epitaxy A. Banerjee, T. Frost, S. Jahangir, E. Stark and P. Bhattacharya	566
Long-wavelength electroluminescence of InGaAs-capped type-II GaSb/GaAs quantum-rings at room temperature W.-H. Lin, K.-W. Wang, S.-Y. Lin and M.-C. Wu	571

InGaP solar cells fabricated using solid-source molecular beam epitaxy T. Sugaya, A. Takeda, R. Oshima, K. Matsubara, S. Niki and Y. Okano	576
Performance of gas source MBE grown InAlGaAs photovoltaic detectors tailored to 1.4 μm L. Zhou, Y. Gu, Y.G. Zhang, K. Wang, X. Fang, Y.Y. Cao, A.Z. Li and Hsby. Li	579
Broadband InGaAs quantum dot-in-a-well solar cells of p-type wells T.E. Tzeng, K.Y. Chuang, T.S. Lay and C.H. Chang	583
The effects of injector doping densities on lasing properties of InP-based quantum cascade lasers at 4.3 μm Y.Y. Li, A.Z. Li, Y. Gu, Y.G. Zhang, H.S.B.Y. Li, K. Wang and X. Fang	587
MBE grown Ga_2O_3 and its power device applications K. Sasaki, M. Higashiwaki, A. Kuramata, T. Masui and S. Yamakoshi	591
InAs/GaSb type-II superlattice mid-wavelength infrared focal plane array detectors grown by molecular beam epitaxy J. Chen, Y. Zhou, Z. Xu, J. Xu, Q. Xu, H. Chen and L. He	596
High-performance AlGaIn/GaN High-electron-mobility transistors employing H_2O annealing W. Ahn, O. Seok, S.M. Song, M.-K. Han and M.-W. Ha	600
The investigation of GaInP solar cell grown by all-solid MBE P. Dai, S.L. Lu, Y.Q. Zhu, L. Ji, W. He, M. Tan, H. Yang, M. Arimochi, H. Yoshida, S. Uchida and M. Ikeda	604
Highly strained photovoltaic dual-channel intersubband photodetectors grown by gas-source MBE M. Elagin, P. Schulz, M. Elagin, M.P. Semtsiv, H. Kirmse, A. Mogilatenko and W.T. Masselink	607
Uncooled InGaSb photovoltaic infrared detectors for gas sensing T. Katsumata, R. Nishimura, K. Yamaoka, E.G. Camargo, T. Morishita, K. Ueno, S. Tokuo, H. Goto and N. Kuze	611
Correlation of the MBE growth temperature, material quality, and performance of quantum cascade lasers G. Monastyrskiy, A. Aleksandrova, M. Elagin, M.P. Semtsiv, W.T. Masselink and V. Bryksa	614
InP/InGaAs/InP DHBT structures with high carbon-doped base grown by gas source molecular beam epitaxy T. Teng, A. Xu, L. Ai, H. Sun and M. Qi	618
Microdisk cavity laser with InGaAs quantum dots on AlAs/GaAs distributed Bragg reflector J.Y. Hsing, T.E. Tzeng, M.Y. Kuo, T.S. Lay and M.H. Shih	622
Growth of high-density 1.06- μm InGaAs/GaAs quantum dots for high gain lasers by molecular beam epitaxy K. Watanabe, T. Akiyama, Y. Yokoyama, K. Takemasa, K. Nishi, Y. Tanaka, M. Sugawara and Y. Arakawa	627
All <i>in-situ</i> GaSb MOS structures on GaAs (001): Growth, passivation and high-k oxides V. Tokranov, S. Madisetti, M. Yakimov, P. Nagaiah, N. Faleev and S. Oktyabrsky	631
Enhancement of light emission from Ge quantum dots by photonic crystal nanocavities at room-temperature X. Xu, N. Usami, T. Maruizumi and Y. Shiraki	636